



SLPS242B – DECEMBER 2009 – REVISED MAY 2010

DualCool[™] N-Channel NexFET[™] Power MOSFETs

Check for Samples: CSD16321Q5C

FEATURES

- DualCool[™] Package SON 5×6mm
- Optimized for Two Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET[™] power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.





PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	25		V
Qg	Gate Charge Total (4.5V)	14		nC
Q _{gd}	Gate Charge Gate to Drain	2.5		nC
		$V_{GS} = 3V$	2.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	2.1	mΩ
		$V_{GS} = 8V$	1.9	mΩ
V _{GS(th)}	Threshold Voltage	1.1		V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16321Q5C	SON 5×6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^{\circ}C$ unless otherwise stated		VALUE	UNIT	
V_{DS}	Drain to Source Voltage	25	V	
V_{GS}	Gate to Source Voltage	+10 /8	V	
	Continuous Drain Current, T _C = 25°C	100	А	
ID	Continuous Drain Current ⁽¹⁾	31	А	
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	200	А	
PD	Power Dissipation ⁽¹⁾	3.1	W	
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C	
E _{AS}	Avalanche Energy, single pulse $I_D = 66A$, L = 0.1mH, $R_G = 25\Omega$	218	mJ	

(1) Typical $R_{\theta JA}$ = 39°C/W on 1-in 2 Cu (2-oz.) on a 0.060" thick FR4 PCB

(2) Pulse duration $\leq 300 \mu s$, duty cycle $\leq 2\%$



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Static Cl	haracteristics				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	25		V
I _{DSS}	Drain to Source Leakage	$V_{GS} = 0V, V_{DS} = 20V$		1	μA
I _{GSS}	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +10/-8V$		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.1	1.4	V
		$V_{GS} = 3V, I_D = 25A$	2.8	3.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5 V, I_D = 25 A$	2.1	2.6	mΩ
		$V_{GS} = 8.0V, I_D = 25A$	1.9	2.4	mΩ
g _{fs}	Transconductance	V _{DS} = 12.5V, I _D = 25A	150		S
Dynamic	Characteristics	•			
C _{iss}	Input Capacitance		2360	3100	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ f = 1MHz	1700	2200	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11112	115	150	pF
R _G	Series Gate Resistance		1.5	3	Ω
Qg	Gate Charge Total (4.5V)		14	19	nC
Q _{gd}	Gate Charge – Gate to Drain	V _{DS} = 12.5V,	2.5		nC
Q _{gs}	Gate Charge – Gate to Source	$I_{DS} = 25A$	4		nC
Q _{g(th)}	Gate Charge at Vth		2.1		nC
Q _{oss}	Output Charge	$V_{DS} = 13.3V, V_{GS} = 0V$	36		nC
t _{d(on)}	Turn On Delay Time		9		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$	15		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 25A, R_G = 2\Omega$	27		ns
t _f	Fall Time		17		ns
Diode C	haracteristics				
V _{SD}	Diode Forward Voltage	$I_{DS} = 25A, V_{GS} = 0V$	0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 13.3V, I _F = 25A,	33		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs	32		ns

THERMAL CHARACTERISTICS

($T_A = 25^{\circ}C$ unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
R_{\thetaJC}	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			1.2	°C/W
R_{\thetaJC}	Thermal Resistance Junction to Case (Bottom drain) ⁽¹⁾			1.1	°C/W
R_{\thetaJA}	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			48	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² 2-oz. Cu pad on a 1.5 x 1.5-inch 0.060-inch thick FR4 board. $R_{\theta JC}$ is specified by design, whereas $R_{\theta CA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² of 2-oz. Cu. (1)

(2)



CSD16321Q5C

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TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$





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TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$



Figure 8. On Resistance vs. Temperature



Figure 10. Maximum Safe Operating Area



Figure 9. Typical Diode Forward Voltage



Figure 11. Single Pulse Unclamped Inductive Switching



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MECHANICAL DATA







Top View

Side View

Bottom View



DualCool [™] Pinout		
Pin#	Label	
1, 2, 3, 9	Source	
4	Gate	
5, 6, 7, 8	Drain	

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DIM	MILLIM	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27 TYP		0.050	
L	0.510	0.710	0.020	0.028
θ	-	-	-	-
К	0.760	-	0.030	-
М	3.260	3.460	0.128	0.136
M1	0.520	0.720	0.020	0.028
N	2.720	2.920	0.107	0.115
N1	1.227	1.427	0.048	0.056

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For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5C Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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REVISION HISTORY

Changes from Original (December 2009) to Revision A	
Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1	
Changes from Revision A (January 2010) to Revision B	Page
 Changed R_{DS(on)} - V_{GS} = 3V, I_D = 25A MAX value From: 3.5 To: 3.8 	2

HISTORY



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